

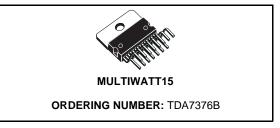
2 x 35W POWER AMPLIFIER FOR CAR RADIO

- HIGH OUTPUT POWER CAPABILITY: 2 x 40W max./4Ω
 2 x 35W/4Ω EIAJ
 2 x 25W4Ω @ 14.4V, 1KHz, 10%
 2 x 37W2Ω @ 14.4V, 1KHz, 10%
- 2Ω DRIVING
- DIFFERENTIAL INPUTS
- MINIMUM EXTERNAL COMPONENT COUNT
- INTERNALLY FIXED GAIN (26dB)
- MUTE FUNCTION (CMOS COMPATIBLE)
- AUTOMUTE AT MINIMUM SUPPLY VOLT-AGE DETECTION
- STAND-BY FUNCTION
- NO AUDIBLE POP DURING MUTE AND ST-BY OPERATIONS
- CLIPPING DETECTOR WITH PROGRAMMA-BLE DISTORTION THRESHOLD

PROTECTIONS:

- SHORT CIRCUIT (OUT TO GROUND, OUT TO SUPPLY VOLTAGE, ACROSS THE LOAD)
- OVERRATING CHIP TEMPERATURE WITH SOFT THERMAL LIMITER
- LOAD DUMP VOLTAGE
- FORTUITOUS OPEN GROUND
- LOUDSPEAKER DC CURRENT
- ESD

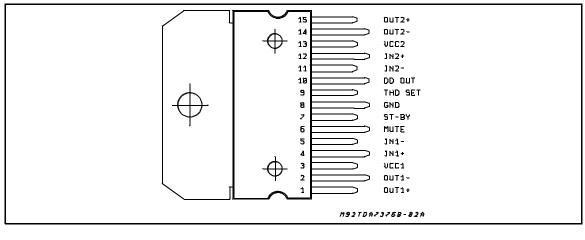
PIN CONNECTION (Continued)



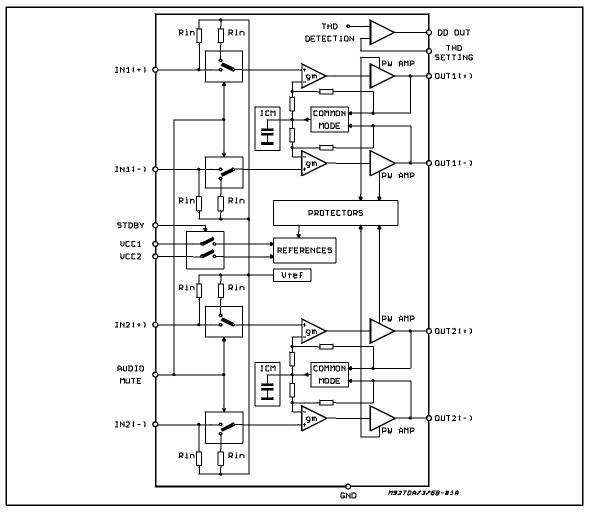
DESCRIPTION

The TDA7376B is a new technology dual bridge Audio Amplifier in Multiwatt 15 package designed for car radio applications. Thanks to the fully complementary PNP/NPN output stage configuration the TDA7376B delivers a rail-to-rail voltage swing with no need of bootstrap capacitors. Differential input pairs, that will accept either single ended or differential input signals, guarantee high noise immunity making the device suitable for both car radio and car boosters applications.

The audio mute control, that attenuates the output signal of the audio amplifiers, suppresses pop on - off transients and cuts any noises coming from previous stages. The St-By control, that debiases the amplifiers, reduces the cost of the power switch. The on-board programmable distortion detector allows compression facility whenever the amplifier is overdriven, so limiting the distortion at any levels inside the presettable range.



BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{OP}	Operating Supply Voltage	18	V	
Vs	DC Supply Voltage	28	V	
V _{peak}	Peak Supply Voltage (t = 50ms)	50	V	
lo	Output Peak Current (non rep. t = 100µs) Output Peak Current (rep. f > 10Hz)	8 6	A A	
P _{tot}	Power Dissipation at $T_{case} = 85^{\circ}C$	36	W	
T _{stg,} T _j	Storage and Junction Temperature	-40 to 150	°C	

THERMAL DATA

Unit
°C/W

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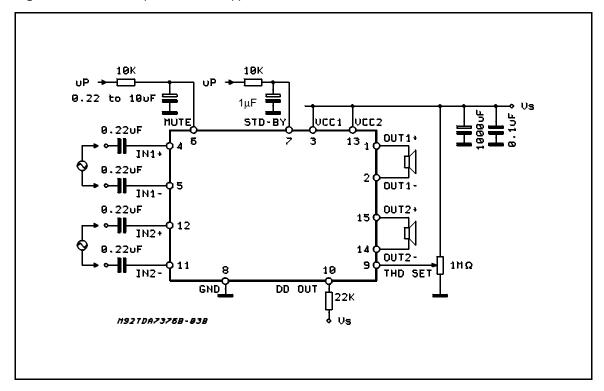
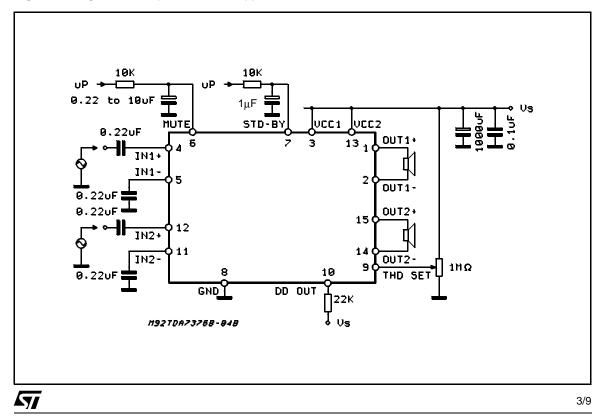
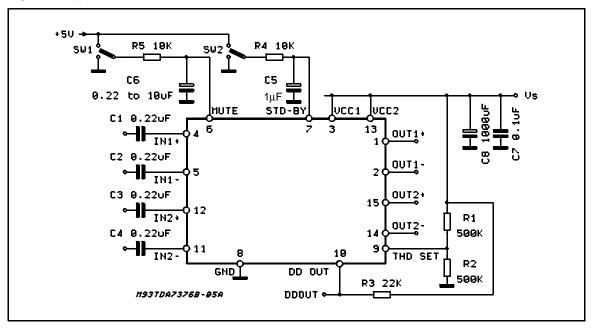


Figure 1: Differential Inputs Test and Application Circuit

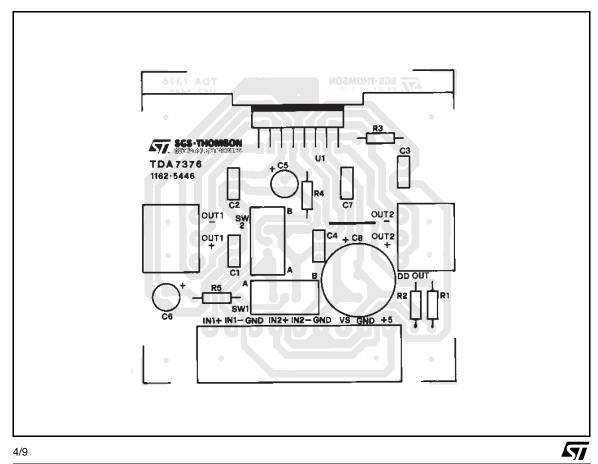
Figure 2: Single Ended Inputs Test and Application Circuit











Symbol	Parameter	Test Condition	Min.	Тур.	Max. 18	Unit V
Vs	Supply Voltage		8			
l _d	Total Quiescent Drain Current	$R_L = \infty$			200	mA
Vos	Output Offset Voltage				120	mV
Po	Output Power	THD = 10% 23 THD = 10%, RL 2Ω 33		25 37		W W
P _{O max}	Max. Output Power (*)	VS = 14.4V	36	40		W
POEIAJ	EIAJ Output Power (*)	V _S = 13.7V	32 35			W
THD	Distortion			0.03 0.08	0.3 0.5	% %
CT	Cross Talk	f = 1KHz; Rg = 0 f = 10KHz; Rg = 0)			dB dB
R _{IN}	Input Resistance	differential input 45 single ended input 40				ΚΩ ΚΩ
Gv	Voltage Gain			26 26	27 27	dB dB
ΔG_V	Channel Gain Balance				1	dB
E _N	Input Noise Voltage	Rg = 600Ω ; "A Weighted" Rg = 600Ω ; 22Hz to 22KHz		3 4	6	μV μV
SVR	Supply Voltage Rejection	f = 100Hz; Vr = 1Vrms; Rg = 0 f = 10KHz; Vr = 1Vrms; Rg = 0	45	55		dB dB
BW	Power Bandwidth	(-3dB)	75			KH
CMRR	Common Mode Rejection Ratio	V _{CM} = 1Vrms input referred	60			dB
A _{SB}	Stand-by Attenuation	V _{SB} = 1.5V; P _{Oref} = 1W	80 90			dB
$V_{\text{sb IN}}$	Stand-by in Threshold				1.5	V
$V_{\text{sb}\text{OUT}}$	Stand-by out Threshold		3.5			V
I _{sb}	Stand-by Current Consumption				100	μA
A _M	Mute Attenuation	V _M = 1.5V; P _{Oref} = 1W		85		dB
V _{MIN}	Mute in Threshold				1.5	V
V _{M OUT}	Mute out Threshold		3.5			V
I ₆	Mute pin Current	$V6 = 0 \text{ to } V_S$, ; $V_{S \text{ max.}} = 18V$			100	μA
D _{DL}	Distortion Detection Level (**)		3.5			%
D _{DOUT}	Distortion Detector Output DC Current	Output low, sinked current (V _{pin10} = 1.5V)	1			mA
		Output high, leakage current ($V_{pin10} = V_S$, @ $V_{Smax} = 18V$)			10	μA

ELECTRICAL CHARACTERISTICS (Refer to the test fig. 1 and 2 circuit, T_{amb} = 25°C; V_S = 14.4V; $f = 1 KHz; R_L = 4\Omega;$ unless otherwise specified.)

(*) Saturated square wave output (**) see figure 5 for THD setting.

The TDA7376B is equipped with a programmable clipping distortion detector circuitry that allows to signal out the output stage saturation by providing a current sinking into an open collector output (DDout) when the total harmonic distortion of the output signal reaches the preset level. The de-sired threshold is fixed through an external divider that produces a proper voltage level across the

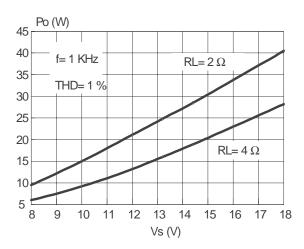
THD set pin. Fig. 5 shows the THD detection threshold versus the THD set voltage. Since it is essential that the THD set voltage be proportional to the supply voltage, fig. 5 shows its value as a fraction of V_{CC} . The actual voltage can be computed by multiplying the fraction corresponding to the desired THD threshold by the application's supply voltage.

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THD (%) 16 $V_{S} = 14.4V$ 14 $R_L = 4\Omega$ f = 1 KHz12 10 8 6 4 2 C 0.1Vs 0.2Vs 0.3Vs 0.4Vs 0.5Vs 0.6Vs THD SET (V)

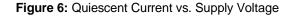
Figure 5: Clip Detector Threshold vs. THD set. Voltage.

Figure 7: Ouput Power vs. Supply Voltage





Po (W) THD (%) 10 = 70 60 $R_L = 4\Omega$ f = 1KHz $V_i = 2.5 V rms$ 50 $R_L = 3.2\Omega$ 40 0.1 $R_L = 4\Omega$ 30 20 0.01 10 0 0.001 8 9 12 13 16 10 11 14 15 17 18 10 Vs (V) 6/9



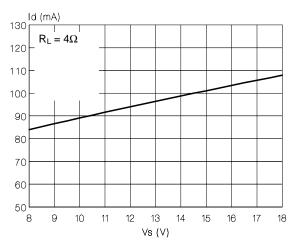
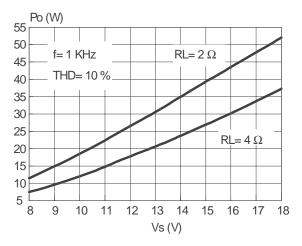
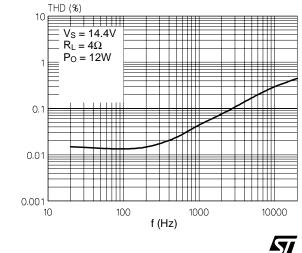
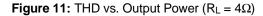


Figure 8: Ouput Power vs. Supply Voltage









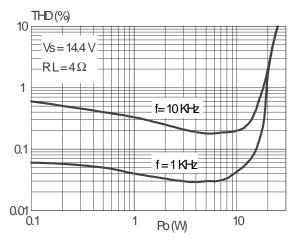
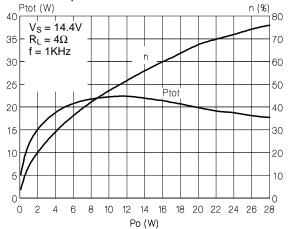


Figure 13: Dissipated Power & Efficiency vs. Output Power





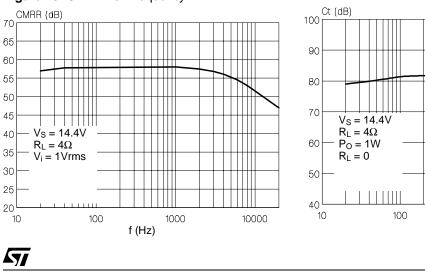


Figure 12: THD vs. Output Power ($R_L = 24\Omega$)

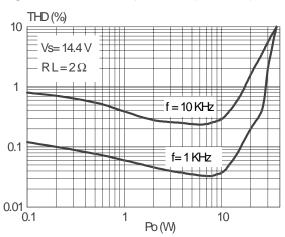
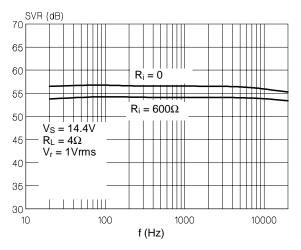
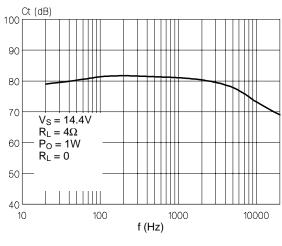


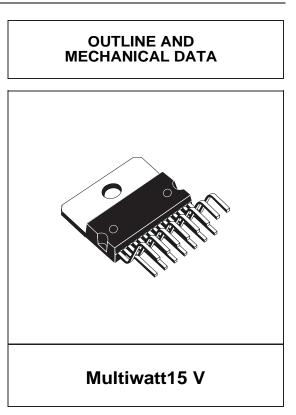
Figure 14: SVR vs. Frequency

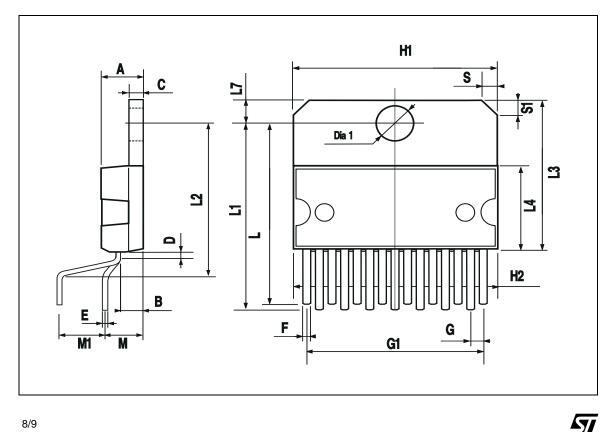






DIM.	mm			inch		
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			5			0.197
В			2.65			0.104
С			1.6			0.063
D		1			0.039	
E	0.49		0.55	0.019		0.022
F	0.66		0.75	0.026		0.030
G	1.02	1.27	1.52	0.040	0.050	0.060
G1	17.53	17.78	18.03	0.690	0.700	0.710
H1	19.6			0.772		
H2			20.2			0.795
L	21.9	22.2	22.5	0.862	0.874	0.886
L1	21.7	22.1	22.5	0.854	0.870	0.886
L2	17.65		18.1	0.695		0.713
L3	17.25	17.5	17.75	0.679	0.689	0.699
L4	10.3	10.7	10.9	0.406	0.421	0.429
L7	2.65		2.9	0.104		0.114
М	4.25	4.55	4.85	0.167	0.179	0.191
M1	4.63	5.08	5.53	0.182	0.200	0.218
S	1.9		2.6	0.075		0.102
S1	1.9		2.6	0.075		0.102
Dia1	3.65		3.85	0.144		0.152





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